

Karen L Kavanagh

List of Publications by Year in descending order

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times ranked

6592
citing authors

| # | ARTICLE | IF | CITATIONS |
|----|--|-----|-----------|
| 1 | Surface Plasmon Sensor Based on the Enhanced Light Transmission through Arrays of Nanoholes in Gold Films. <i>Langmuir</i> , 2004, 20, 4813-4815. | 1.6 | 715 |
| 2 | A New Generation of Sensors Based on Extraordinary Optical Transmission. <i>Accounts of Chemical Research</i> , 2008, 41, 1049-1057. | 7.6 | 492 |
| 3 | Generation of misfit dislocations in semiconductors. <i>Journal of Applied Physics</i> , 1987, 62, 4413-4420. | 1.1 | 464 |
| 4 | Strong Polarization in the Optical Transmission through Elliptical Nanohole Arrays. <i>Physical Review Letters</i> , 2004, 92, 037401. | 2.9 | 439 |
| 5 | Nanohole-Enhanced Raman Scattering. <i>Nano Letters</i> , 2004, 4, 2015-2018. | 4.5 | 418 |
| 6 | Luminescent Colloidal Silicon Suspensions from Porous Silicon. <i>Science</i> , 1992, 255, 66-68. | 6.0 | 237 |
| 7 | Asymmetries in dislocation densities, surface morphology, and strain of GaInAs/GaAs single heterolayers. <i>Journal of Applied Physics</i> , 1988, 64, 4843-4852. | 1.1 | 208 |
| 8 | Nonalloyed ohmic contacts to GaAs by solid-phase epitaxy of Ge. <i>Journal of Applied Physics</i> , 1987, 62, 942-947. | 1.1 | 204 |
| 9 | Enhanced Fluorescence from Arrays of Nanoholes in a Gold Film. <i>Journal of the American Chemical Society</i> , 2005, 127, 14936-14941. | 6.6 | 203 |
| 10 | Thin epitaxial Ge [~] Si(111) films: Study and control of morphology. <i>Surface Science</i> , 1987, 191, 305-328. | 0.8 | 164 |
| 11 | Resonant optical transmission through hole arrays in metal films: physics and applications. <i>Laser and Photonics Reviews</i> , 2010, 4, 311-335. | 4.4 | 150 |
| 12 | Misfit dislocations in nanowire heterostructures. <i>Semiconductor Science and Technology</i> , 2010, 25, 024006. | 1.0 | 149 |
| 13 | Fermi-Level Pinning by Misfit Dislocations at GaAs Interfaces. <i>Physical Review Letters</i> , 1983, 51, 1783-1786. | 2.9 | 132 |
| 14 | Observation of quantum dot-like behavior of GaInNAs in GaInNAs/GaAs quantum wells. <i>Applied Physics Letters</i> , 1999, 74, 2337-2339. | 1.5 | 126 |
| 15 | Lattice Compression from Conduction Electrons in Heavily Doped Si:As. <i>Physical Review Letters</i> , 1988, 61, 1748-1751. | 2.9 | 112 |
| 16 | Growth, branching, and kinking of molecular-beam epitaxial $\text{In}_{1-x}\text{Ga}_x\text{As}$ nanowires. <i>Applied Physics Letters</i> , 2003, 83, 3368-3370. | 1.5 | 112 |
| 17 | Effects of GaAs substrate misorientation on strain relaxation in $\text{In}_x\text{Ga}_{1-x}\text{As}$ films and multilayers. <i>Journal of Applied Physics</i> , 1998, 83, 5137-5149. | 1.1 | 102 |
| 18 | Apex-Enhanced Raman Spectroscopy Using Double-Hole Arrays in a Gold Film. <i>Journal of Physical Chemistry C</i> , 2007, 111, 2347-2350. | 1.5 | 96 |

| # | ARTICLE | IF | CITATIONS |
|----|---|-----|-----------|
| 19 | Strain relaxation of compositionally graded $\text{In}_x\text{Ga}_{1-x}\text{As}$ buffer layers for modulation-doped $\text{In}_{0.3}\text{Ga}_{0.7}\text{As}/\text{In}_{0.29}\text{Al}_{0.71}\text{As}$ heterostructures. <i>Applied Physics Letters</i> , 1992, 60, 1129-1131. | 1.5 | 95 |
| 20 | Heteroepitaxial Growth of Vertical GaAs Nanowires on Si (111) Substrates by Metal-Organic Chemical Vapor Deposition. <i>Nano Letters</i> , 2008, 8, 3755-3760. | 4.5 | 93 |
| 21 | Structural and Room-Temperature Transport Properties of Zinc Blende and Wurtzite InAs Nanowires. <i>Advanced Functional Materials</i> , 2009, 19, 2102-2108. | 7.8 | 86 |
| 22 | Direct Measurement of Coherency Limits for Strain Relaxation in Heteroepitaxial Core/Shell Nanowires. <i>Nano Letters</i> , 2013, 13, 1869-1876. | 4.5 | 80 |
| 23 | Effects of rapid thermal annealing on GaInNAs/GaAs multiple quantum wells. <i>Journal of Crystal Growth</i> , 1999, 201-202, 419-422. | 0.7 | 78 |
| 24 | Enhancement of band edge luminescence in ZnSe nanowires. <i>Journal of Applied Physics</i> , 2006, 100, 084316. | 1.1 | 78 |
| 25 | Electron-Energy-Loss Scattering near a Single Misfit Dislocation at the GaAs/GaNAs Interface. <i>Physical Review Letters</i> , 1986, 57, 2729-2732. | 2.9 | 75 |
| 26 | Basis and Lattice Polarization Mechanisms for Light Transmission through Nanohole Arrays in a Metal Film. <i>Nano Letters</i> , 2005, 5, 1243-1246. | 4.5 | 66 |
| 27 | Surface Plasmon-Quantum Dot Coupling from Arrays of Nanoholes. <i>Journal of Physical Chemistry B</i> , 2006, 110, 8307-8313. | 1.2 | 64 |
| 28 | Silicon diffusion at polycrystalline Si/GaAs interfaces. <i>Applied Physics Letters</i> , 1985, 47, 1208-1210. | 1.5 | 59 |
| 29 | Transport and strain relaxation in wurtzite InAs-GaAs core-shell heterowires. <i>Applied Physics Letters</i> , 2011, 98, . | 1.5 | 57 |
| 30 | Faster radial strain relaxation in InAs-GaAs core-shell heterowires. <i>Journal of Applied Physics</i> , 2012, 111, . | 1.1 | 57 |
| 31 | Lattice-strained heterojunction InGaAs/GaAs bipolar structures: Recombination properties and device performance. <i>Journal of Applied Physics</i> , 1987, 61, 1234-1236. | 1.1 | 56 |
| 32 | Lattice tilt and dislocations in compositionally step-graded buffer layers for mismatched InGaAs/GaAs heterointerfaces. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1992, 10, 1820. | 1.6 | 49 |
| 33 | Growth-induced magnetic anisotropy and clustering in vapor-deposited Co-Pt alloy films. <i>Physical Review B</i> , 1999, 60, 12826-12836. | 1.1 | 49 |
| 34 | Ohmic contacts to GaAs using In/Pd metallization. <i>Applied Physics Letters</i> , 1987, 51, 326-327. | 1.5 | 48 |
| 35 | Probing the electrical transport properties of intrinsic InN nanowires. <i>Applied Physics Letters</i> , 2013, 102, . | 1.5 | 48 |
| 36 | Developing 1D nanostructure arrays for future nanophotonics. <i>Nanoscale Research Letters</i> , 2006, 1, 99-119. | 3.1 | 46 |

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|----|---|------|-----------|
| 37 | Porous silicon - what is responsible for the visible luminescence?. <i>Advanced Materials</i> , 1992, 4, 432-434. | 11.1 | 45 |
| 38 | Nanometer-resolved spatial variations in the Schottky barrier height of a Au/n-type GaAs diode. <i>Physical Review B</i> , 1994, 49, 16474-16479. | 1.1 | 45 |
| 39 | The interdiffusion of Si, P, and In at polysilicon/GaAs interfaces. <i>Journal of Applied Physics</i> , 1988, 64, 1845-1854. | 1.1 | 40 |
| 40 | Nanoscale Electrical and Structural Characterization of Gold/Alkyl Monolayer/Silicon Diode Junctions. <i>Journal of Physical Chemistry C</i> , 2008, 112, 9081-9088. | 1.5 | 39 |
| 41 | Geometric limits of coherent III-V core/shell nanowires. <i>Journal of Applied Physics</i> , 2013, 114, . | 1.1 | 39 |
| 42 | Gas-source molecular beam epitaxial growth and thermal annealing of GaInNAs/GaAs quantum wells. <i>Journal of Crystal Growth</i> , 2000, 208, 145-152. | 0.7 | 38 |
| 43 | Structure and photoluminescence of ZnSe nanostructures fabricated by vapor phase growth. <i>Journal of Applied Physics</i> , 2007, 101, 014326. | 1.1 | 38 |
| 44 | Relationship between surface morphology and strain relaxation during growth of InGaAs strained layers. <i>Applied Physics Letters</i> , 1995, 67, 3744-3746. | 1.5 | 37 |
| 45 | Correlation of anisotropic strain relaxation with substrate misorientation direction at InGaAs/GaAs(001) interfaces. <i>Applied Physics Letters</i> , 1995, 67, 344-346. | 1.5 | 37 |
| 46 | Twinning modulation in ZnSe nanowires. <i>Semiconductor Science and Technology</i> , 2007, 22, 175-178. | 1.0 | 37 |
| 47 | Molecular Orientation in Octanedithiol and Hexadecanethiol Monolayers on GaAs and Au Measured by Infrared Spectroscopic Ellipsometry. <i>Langmuir</i> , 2009, 25, 919-923. | 1.6 | 37 |
| 48 | Scanning spreading resistance microscopy current transport studies on doped III-V semiconductors. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2002, 20, 1682. | 1.6 | 36 |
| 49 | Defect studies of ZnSe nanowires. <i>Nanotechnology</i> , 2008, 19, 215715. | 1.3 | 36 |
| 50 | Ballistic Electron Emission Microscopy Studies of Au/Molecule/n-GaAs Diodes. <i>Journal of Physical Chemistry B</i> , 2005, 109, 6252-6256. | 1.2 | 33 |
| 51 | Field Dependent Transport Properties in InAs Nanowire Field Effect Transistors. <i>Nano Letters</i> , 2008, 8, 3114-3119. | 4.5 | 33 |
| 52 | Calibrated scanning spreading resistance microscopy profiling of carriers in III-V structures. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2001, 19, 1662. | 1.6 | 32 |
| 53 | Anisotropic resistivity correlated with atomic ordering in p-type GaAsSb. <i>Applied Physics Letters</i> , 2001, 79, 2384-2386. | 1.5 | 31 |
| 54 | Growth of InAsSb/InAs MQWs on GaSb for mid-IR photodetector applications. <i>Journal of Crystal Growth</i> , 2009, 311, 3563-3567. | 0.7 | 31 |

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|----|---|-----|-----------|
| 55 | Time dependent ballistic electron emission microscopy studies of a Au/(100)GaAs interface with a native oxide diffusion barrier. Applied Physics Letters, 1993, 62, 2965-2967. | 1.5 | 30 |
| 56 | Gas-source molecular beam epitaxial growth, characterization, and light-emitting diode application of In _x Ga _{1-x} P on GaP(100). Applied Physics Letters, 1993, 62, 2369-2371. | 1.5 | 29 |
| 57 | Rectifying characteristics of Te-doped GaAs nanowires. Applied Physics Letters, 2011, 99, 182102. | 1.5 | 29 |
| 58 | Multiple dislocation loops in linearly graded In _x Ga _{1-x} As (0 ≤ x ≤ 0.53) on GaAs and In _x Ga _{1-x} P (0 ≤ x ≤ 0.32) on GaP. Applied Physics Letters, 1993, 63, 500-502. | 1.5 | 28 |
| 59 | Lateral variation in the Schottky barrier height of Au/PtSi/(100)Si diodes. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1994, 12, 2634. | 1.6 | 26 |
| 60 | Substrate effects on the ferroelectric properties of fine-grained BaTiO ₃ films. Journal of Applied Physics, 2003, 94, 5982-5989. | 1.1 | 26 |
| 61 | Study of 1/4-scale spatial variations in strain of a compositionally step-graded In _x Ga _{1-x} As/GaAs(001) heterostructure. Applied Physics Letters, 1995, 66, 869-871. | 1.5 | 25 |
| 62 | Improved Performance of Nanohole Surface Plasmon Resonance Sensors by the Integrated Response Method. IEEE Photonics Journal, 2011, 3, 441-449. | 1.0 | 25 |
| 63 | Reduction of Gold Penetration through Phenyl-Terminated Alkyl Monolayers on Silicon. Journal of Physical Chemistry C, 2012, 116, 17040-17047. | 1.5 | 25 |
| 64 | Aligned Co nanodiscs by electrodeposition on GaAs. Journal of Crystal Growth, 2006, 287, 514-517. | 0.7 | 24 |
| 65 | Metastable phase formation in the Au-Si system via ultrafast nanocalorimetry. Journal of Applied Physics, 2012, 111, . | 1.1 | 24 |
| 66 | Space-charge-limited current in nanowires. Journal of Applied Physics, 2017, 121, . | 1.1 | 24 |
| 67 | Hot-electron attenuation lengths in ultrathin magnetic films. Journal of Applied Physics, 2000, 87, 5164-5166. | 1.1 | 23 |
| 68 | Antimony segregation in GaAs-based multiple quantum well structures. Journal of Crystal Growth, 2003, 254, 28-34. | 0.7 | 23 |
| 69 | Preparation of ideal molecular junctions: depositing non-invasive gold contacts on molecularly modified silicon. Nanoscale, 2011, 3, 1434. | 2.8 | 23 |
| 70 | Direct Measurement of the Electrical Abruptness of a Nanowire p-n Junction. Nano Letters, 2016, 16, 3982-3988. | 4.5 | 23 |
| 71 | Anisotropic structural, electronic, and optical properties of InGaAs grown by molecular beam epitaxy on misoriented substrates. Applied Physics Letters, 1994, 65, 1424-1426. | 1.5 | 22 |
| 72 | Comparison of strain relaxation in InGaAsN and InGaAs thin films. Applied Physics Letters, 2002, 80, 4357-4359. | 1.5 | 22 |

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| 73 | Epitaxial Fe ^δ -GaAs via electrochemistry. Journal of Applied Physics, 2005, 98, 066103. | 1.1 | 22 |
| 74 | Growth and strain relaxation of GaAs and GaP nanowires with GaSb shells. Journal of Applied Physics, 2013, 113, 134309. | 1.1 | 22 |
| 75 | Modulation-doped In _{0.3} Ga _{0.7} As/In _{0.29} Al _{0.71} As heterostructures grown on GaAs by step grading. Semiconductor Science and Technology, 1992, 7, 601-603. | 1.0 | 21 |
| 76 | Lattice strain from substitutional Ga and from holes in heavily doped Si:Ga. Physical Review B, 1992, 45, 3323-3331. | 1.1 | 21 |
| 77 | Planar Ge/Pd and alloyed Au-Ge-Ni ohmic contacts to Al _x Ga _{1-x} As (0 ≤ x ≤ 0.3). Applied Physics Letters, 1989, 54, 721-723. | 1.5 | 19 |
| 78 | Quantum dot-like behavior of GaInNAs in GaInNAs/GaAs quantum wells grown by gas-source molecular-beam epitaxy. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1999, 17, 1649. | 1.6 | 19 |
| 79 | Structural and magnetic properties of NiMnSb/InGaAs/InP(001). Journal of Applied Physics, 2005, 97, 073906. | 1.1 | 19 |
| 80 | Epitaxial Bi ^δ -GaAs diodes via electrodeposition. Journal of Vacuum Science & Technology B, 2006, 24, 2138. | 1.3 | 19 |
| 81 | High-resolution X-ray diffraction of InAlAs/InP superlattices grown by gas source molecular beam epitaxy. Applied Physics Letters, 1991, 58, 1530-1532. | 1.5 | 17 |
| 82 | Epitaxial Bi ^δ -GaAs(111) diodes via electrodeposition. Applied Physics Letters, 2006, 88, 022102. | 1.5 | 17 |
| 83 | The Polycrystalline-Si Contact to GaAs. Journal of the Electrochemical Society, 1986, 133, 1176-1179. | 1.3 | 15 |
| 84 | Optical detection of misfit dislocation-induced deep levels at InGaAs/GaAs heterojunctions. Applied Physics Letters, 1994, 64, 3572-3574. | 1.5 | 15 |
| 85 | Au/ZnSe contacts characterized by ballistic electron emission microscopy. Journal of Applied Physics, 1996, 79, 1532-1535. | 1.1 | 15 |
| 86 | Role of interface microstructure in rectifying metal/semiconductor contacts: Ballistic electron emission observations correlated to microstructure. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1996, 14, 1238. | 1.6 | 15 |
| 87 | Large-Area Low-Cost Flexible Plastic Nanohole Arrays for Integrated Bio-Chemical Sensing. IEEE Sensors Journal, 2013, 13, 3982-3990. | 2.4 | 15 |
| 88 | Relaxation-induced polarized luminescence from In _x Ga _{1-x} As films grown on GaAs(001). Physical Review B, 1995, 51, 5033-5037. | 1.1 | 14 |
| 89 | p-type doping of GaAs nanowires using carbon. Journal of Applied Physics, 2012, 112, 094323. | 1.1 | 14 |
| 90 | Lithography-Free Fabrication of Core-Shell GaAs Nanowire Tunnel Diodes. Nano Letters, 2015, 15, 5408-5413. | 4.5 | 14 |

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| 91 | Correlation of buffer strain relaxation modes with transport properties of two-dimensional electron gases. <i>Journal of Applied Physics</i> , 1996, 80, 6849-6854. | 1.1 | 13 |
| 92 | Faceting transition in epitaxial growth of dilute GaNAs films on GaAs. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2001, 19, 1417. | 1.6 | 12 |
| 93 | Residual Stress, Defects, and Electrical Properties of Epitaxial Copper Growth on GaAs. <i>Journal of the Electrochemical Society</i> , 2009, 156, D138. | 1.3 | 12 |
| 94 | Electrodeposition, characterization and morphological investigations of NiFe/Cu multilayers prepared by pulsed galvanostatic, dual bath technique. <i>Materials Characterization</i> , 2011, 62, 204-210. | 1.9 | 12 |
| 95 | Controlled axial and radial Te-doping of GaAs nanowires. <i>Journal of Applied Physics</i> , 2012, 112, 054324. | 1.1 | 12 |
| 96 | Tensile strain relaxation in GaN _x P _{1-x} (x ≈ 0.1) grown by chemical beam epitaxy. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1996, 14, 2952. | 1.6 | 11 |
| 97 | Ballistic electron and photocurrent transport in Au-molecular layer-GaAs diodes. <i>Journal of Applied Physics</i> , 2007, 102, . | 1.1 | 11 |
| 98 | Effect of Bi surfactant on atomic ordering of GaAsSb. <i>Applied Physics Letters</i> , 2004, 85, 5589-5591. | 1.5 | 10 |
| 99 | Long-lasting flexible organic solar cells stored and tested entirely in air. <i>Applied Physics Letters</i> , 2011, 99, 263305. | 1.5 | 10 |
| 100 | Role of Hydrogen Evolution during Epitaxial Electrodeposition of Fe on GaAs. <i>Journal of the Electrochemical Society</i> , 2018, 165, H3076-H3079. | 1.3 | 10 |
| 101 | Growth of h-BN on copper (110) in a LEEM. <i>Surface Science</i> , 2018, 669, 133-139. | 0.8 | 10 |
| 102 | Hole confinement and low-frequency noise in SiGe pFETs on silicon-on-sapphire. <i>IEEE Electron Device Letters</i> , 1999, 20, 173-175. | 2.2 | 9 |
| 103 | The growth of SiGe on sapphire using rapid thermal chemical vapor deposition. <i>Journal of Crystal Growth</i> , 2001, 222, 20-28. | 0.7 | 9 |
| 104 | Effects of capillary forces on copper dielectric interfacial void evolution. <i>Applied Physics Letters</i> , 2004, 84, 5201-5203. | 1.5 | 9 |
| 105 | Planar defects and phase transformation in ZnSe nanosaws. <i>Journal of Materials Science: Materials in Electronics</i> , 2006, 17, 1065-1070. | 1.1 | 9 |
| 106 | Epitaxial Fe _x Ni _{1-x} Thin Film Contacts to GaAs via Electrochemistry. <i>Journal of the Electrochemical Society</i> , 2008, 155, H841. | 1.3 | 9 |
| 107 | Detecting Antibodies Secreted by Trapped Cells Using Extraordinary Optical Transmission. <i>IEEE Sensors Journal</i> , 2011, 11, 2732-2739. | 2.4 | 9 |
| 108 | Si diffusion and segregation in low-temperature grown GaAs. <i>Applied Physics Letters</i> , 1993, 62, 286-288. | 1.5 | 8 |

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|-----|--|------|-----------|
| 109 | Comparison of Au contacts to Si, GaAs, In _x Ga _{1-x} P, and ZnSe measured by ballistic electron emission microscopy. <i>Materials Chemistry and Physics</i> , 1996, 46, 224-229. | 2.0 | 8 |
| 110 | Modulation-doped In _{0.53} Ga _{0.47} As/In _{0.52} Al _{0.48} As heterostructures grown on GaAs substrates using step-graded In _x Ga _{1-x} As buffers. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1996, 14, 3035. | 1.6 | 8 |
| 111 | Wavelength-Invariant Resist Composed of Bimetallic Layers. <i>Materials Research Society Symposia Proceedings</i> , 2002, 745, 381. | 0.1 | 8 |
| 112 | Plasmonic sensors based on nano-holes: technology and integration. <i>Proceedings of SPIE</i> , 2008, , . | 0.8 | 8 |
| 113 | Aligned cuboid iron nanoparticles by epitaxial electrodeposition. <i>Nanoscale</i> , 2017, 9, 5315-5322. | 2.8 | 8 |
| 114 | Electrical properties of lightly Ga-doped ZnO nanowires. <i>Semiconductor Science and Technology</i> , 2017, 32, 125010. | 1.0 | 8 |
| 115 | Room-temperature electrosynthesis of carbonaceous fibers. <i>Advanced Materials</i> , 1995, 7, 398-401. | 11.1 | 7 |
| 116 | X-Ray Diffuse Scattering from Misfit Dislocation at Buried Interface. <i>Materials Research Society Symposia Proceedings</i> , 2001, 673, 1. | 0.1 | 7 |
| 117 | Strain relaxation by ~100% misfit dislocations in dilute nitride In _x Ga _{1-x} As _{1-y} Ny/GaAs quantum wells. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2005, 202, 2849-2857. | 0.8 | 7 |
| 118 | Lateral spin injection and detection through electrodeposited Fe/GaAs contacts. <i>Semiconductor Science and Technology</i> , 2013, 28, 035003. | 1.0 | 7 |
| 119 | Anisotropic Surface Roughness in Strain Relaxed In _{0.40} Ga _{0.60} As on GaAs with a Step-Graded In _x Ga _{1-x} As Buffer Layer. <i>Materials Research Society Symposia Proceedings</i> , 1993, 312, 107. | 0.1 | 6 |
| 120 | Interfacial scattering of hot electrons in ultrathin Au/Co films. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2000, 18, 2047. | 1.6 | 6 |
| 121 | Au-Ag and Au-Pd molecular contacts to GaAs. <i>Journal of Vacuum Science & Technology B</i> , 2008, 26, 1597-1601. | 1.3 | 6 |
| 122 | Atomic ordering in GaAsSb (001) grown by metalorganic vapor phase epitaxy. <i>Journal of Crystal Growth</i> , 2009, 311, 4391-4397. | 0.7 | 6 |
| 123 | Recycling gold nanohole arrays. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2014, 32, . | 0.9 | 6 |
| 124 | Interfacial reactions at Fe/topological insulator spin contacts. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2017, 35, 04F105. | 0.6 | 6 |
| 125 | Structural and electrical characteristics of microcrystalline silicon prepared by hot-wire chemical vapor deposition using a graphite filament. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2007, 25, 464-467. | 0.9 | 5 |
| 126 | Transparent conducting indium bismuth oxide. <i>Thin Solid Films</i> , 2007, 515, 3760-3765. | 0.8 | 5 |

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|-----|---|-----|-----------|
| 127 | Improved chemical and electrical stability of gold silicon contacts via epitaxial electrodeposition. Journal of Applied Physics, 2013, 113, 063708. | 1.1 | 5 |
| 128 | Title is missing!. Journal of Medical and Biological Engineering, 2011, 31, 121. | 1.0 | 5 |
| 129 | Cw laser crystallization of glow discharge a-Si:H on glass substrates. Journal of Electronic Materials, 1982, 11, 303-320. | 1.0 | 4 |
| 130 | The Diffusion of Phosphorus and Indium into Gallium Arsenide from Polycrystalline-Silicon. Materials Research Society Symposia Proceedings, 1986, 77, 785. | 0.1 | 4 |
| 131 | Oxidation induced AlAs/GaAs superlattice disordering. Applied Physics Letters, 1992, 60, 1235-1237. | 1.5 | 4 |
| 132 | Beem Investigation of Oxide and Sulfide Passivated GaAs. Materials Research Society Symposia Proceedings, 1992, 281, 653. | 0.1 | 4 |
| 133 | Dislocation-Induced deep level states in In _{0.08} Ga _{0.92} As/GaAs heterostructures. Journal of Electronic Materials, 1994, 23, 929-933. | 1.0 | 4 |
| 134 | Evolution of interface voids under current and temperature stress in integrated circuit metallization. Metals and Materials International, 2004, 10, 411-415. | 1.8 | 4 |
| 135 | Nanoholes in metals with applications to sensors and spectroscopy. International Journal of Nanotechnology, 2008, 5, 1058. | 0.1 | 4 |
| 136 | Sensing of antibodies secreted by microfluidically trapped cells via extraordinary optical transmission through nanohole arrays. , 2010, , . | | 4 |
| 137 | Effect of annealing on the structural and optical properties of heavily carbon-doped ZnO. Semiconductor Science and Technology, 2010, 25, 045023. | 1.0 | 4 |
| 138 | Electrical characterization of Si/InN nanowire heterojunctions. Semiconductor Science and Technology, 2018, 33, 015008. | 1.0 | 4 |
| 139 | Three-Dimensional Imaging of Beam-Induced Biasing of InP/GaInP Tunnel Diodes. Nano Letters, 2019, 19, 3490-3497. | 4.5 | 4 |
| 140 | Axial EBIC oscillations at core/shell GaAs/Fe nanowire contacts. Nanotechnology, 2019, 30, 025701. | 1.3 | 4 |
| 141 | Three-Dimensional Conductive Fingerprint Phantoms Made of Ethylene-Vinyl Acetate/Graphene Nanocomposite for Evaluating Smartphone Scanners. ACS Applied Electronic Materials, 2021, 3, 2097-2105. | 2.0 | 4 |
| 142 | <title>Control of surface morphology and strain relaxation in InGaAs grown on GaAs using a step-graded buffer</title>. , 1994, 2140, 179. | | 3 |
| 143 | Microstructure of ordered nanodomains induced by Bi surfactant in OMVPE-grown GaAsSb. Journal of Crystal Growth, 2006, 287, 541-544. | 0.7 | 3 |
| 144 | Characterization of solution-bonded GaAs/InGaAs/GaAs features on GaAs. Semiconductor Science and Technology, 2014, 29, 075009. | 1.0 | 3 |

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|-----|---|-----|-----------|
| 145 | Regrowth mechanism for oxide isolation of GaAs nanowires. <i>Nanotechnology</i> , 2017, 28, 385302. | 1.3 | 3 |
| 146 | Measuring Surface Energies of GaAs (100) and Si (100) by Three Liquid Contact Angle Analysis (3LCAA) for Heterogeneous Nano-Bonding. <i>MRS Advances</i> , 2018, 3, 3403-3411. | 0.5 | 3 |
| 147 | A New Technique for Magnetic Nanoparticle Imaging Using Magnetoencephalography Frequency Data. <i>IFMBE Proceedings</i> , 2010, , 443-446. | 0.2 | 3 |
| 148 | Rotational epitaxy of h-BN on Cu (110). <i>Surface Science</i> , 2022, 721, 122080. | 0.8 | 3 |
| 149 | Luminescent Colloidal Si Suspensions from Porous Si. <i>Materials Research Society Symposia Proceedings</i> , 1991, 256, 131. | 0.1 | 2 |
| 150 | Strain relaxation induced deep levels in In _{1-x} Ga _x As thin films. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 1994, 12, 1050-1053. | 0.9 | 2 |
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